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## Sommario/riassunto

This book provides an in-depth analysis of advanced nanoscale MOSFET architectures, focusing on current trends and future perspectives in the field. Edited by experts Kalyan Biswas and Angsuman Sarkar, the book covers a range of topics including MOSFET scaling, device physics, and the operation of novel transistor technologies such as TunnelFET, NanowireFET, and GrapheneFET. It also explores high-k dielectrics, the impact of trap charges on dielectric defects, and the performance of nanosheet transistors. Intended for researchers, engineers, and professionals, the book offers insights into the challenges and opportunities presented by nanoscale devices in modern technology.

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